

1. Record Nr.	UNINA9910705626303321
Autore	Freeman Jon C.
Titolo	Basic equations for the modeling of gallium nitride (GaN) high electron mobility transistors (HEMTs) // Jon C. Freeman
Pubbl/distr/stampa	Cleveland, Ohio : , : National Aeronautics and Space Administration, Glenn Research Center, , February 2003
Descrizione fisica	1 online resource (65 pages) : illustrations
Collana	NASA/TM ; ; 2003-211983
Soggetti	Gallium nitrides Field effect transistors High electron mobility transistors
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	"February 2003." "Performing organization: National Aeronautics and Space Administration, John H. Glenn Research Center at Lewis Field" Report documentation page.
Nota di bibliografia	Includes bibliographical references (pages 62-65).